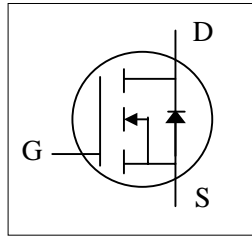


# N-CHANNEL ENHANCEMENT MODE POWER MOSFET

## PRODUCT SUMMARY

Simple Drive Requirement  
Low On-Resistance  
Fast Switching Characteristic

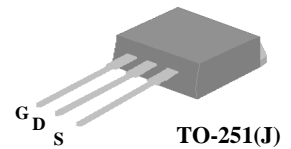
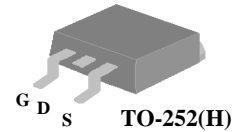


$BV_{DSS}$	25V
$R_{DS(ON)}$	9m $\Omega$
$I_D$	62A

## DESCRIPTION

The advanced power MOSFETs from Silicon Standard Corp. provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-252 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (SSM72T02GH) are available for low-profile applications.



 **Pb-free; RoHS-compliant**

## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	25	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	62	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	44	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	190	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	60	W
	Linear Derating Factor	0.4	W/ $^\circ\text{C}$
$E_{AS}$	Single Pulse Avalanche Energy <sup>3</sup>	29	mJ
$I_{AR}$	Avalanche Current	24	A
$T_{STG}$	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

## THERMAL DATA

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-case Max.	2.5	$^\circ\text{C}/\text{W}$
Rthj-a	Thermal Resistance Junction-ambient Max.	110	$^\circ\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS

( $T_J=25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	25	-	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	-	0.02	-	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	-	8	9	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=15A$	-	11	15	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
$g_{fs}$	Forward Transconductance	$V_{DS}=10V, I_D=30A$	-	42	-	S
$I_{DSS}$	Drain-Source Leakage Current ( $T_J=25^\circ\text{C}$ )	$V_{DS}=25V, V_{GS}=0V$	-	-	1	$\mu A$
	Drain-Source Leakage Current ( $T_J=175^\circ\text{C}$ )	$V_{DS}=20V, V_{GS}=0V$	-	-	25	$\mu A$
$I_{GSS}$	Gate-Source Leakage	$V_{GS}=\pm 20V$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_D=30A$	-	13	21	nC
$Q_{gs}$	Gate-Source Charge	$V_{DS}=20V$	-	2.7	-	nC
$Q_{gd}$	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	9	-	nC
$t_{d(on)}$	Turn-on Delay Time <sup>2</sup>	$V_{DS}=15V$	-	8	-	ns
$t_r$	Rise Time	$I_D=30A$	-	80	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	22	-	ns
$t_f$	Fall Time	$R_D=0.5\Omega$	-	6	-	ns
$C_{iss}$	Input Capacitance	$V_{GS}=0V$	-	930	1490	pF
$C_{oss}$	Output Capacitance	$V_{DS}=25V$	-	250	-	pF
$C_{rss}$	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	180	-	pF
$R_g$	Gate Resistance	$f=1.0\text{MHz}$	-	1.1	1.7	$\Omega$

## SOURCE-DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{SD}$	Forward On Voltage <sup>2</sup>	$I_S=30A, V_{GS}=0V$	-	-	1.3	V
$t_{rr}$	Reverse Recovery Time <sup>2</sup>	$I_S=15A, V_{GS}=0V,$	-	26	-	ns
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s$	-	15	-	nC

### Notes:

1. Pulse width limited by max. junction temperature.
2. Pulse test
3. Starting  $T_J=25^\circ\text{C}$ ,  $V_{DD}=25V$ ,  $L=0.1\text{mH}$ ,  $R_G=25\Omega$ ,  $I_{AS}=24A$ .

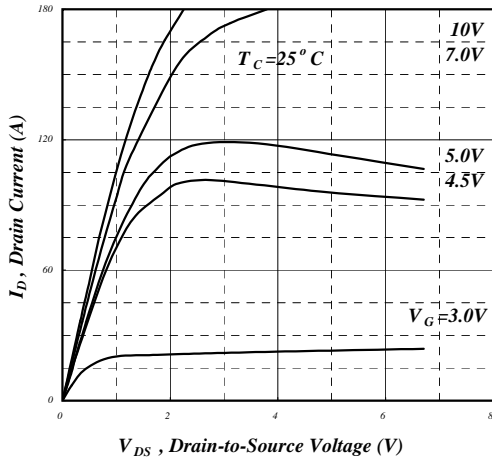


Fig 1. Typical Output Characteristics

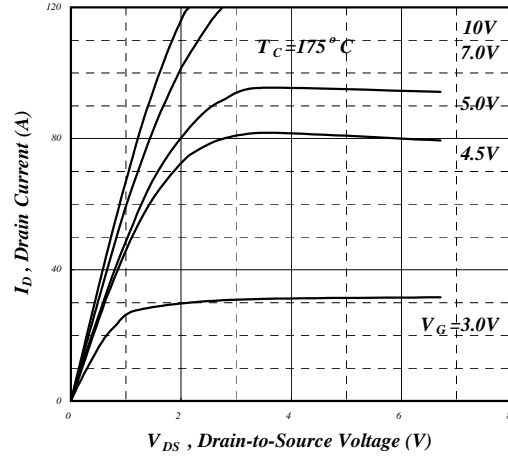


Fig 2. Typical Output Characteristics

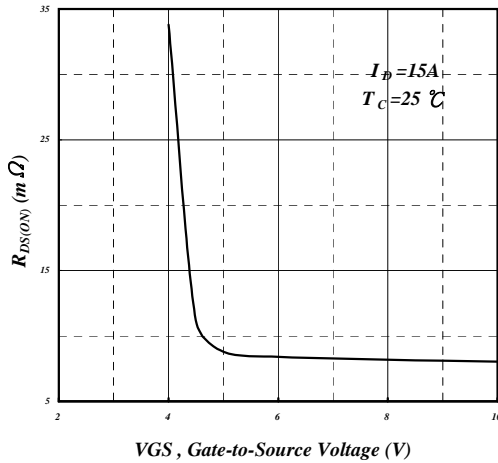


Fig 3. On-Resistance v.s. Gate Voltage

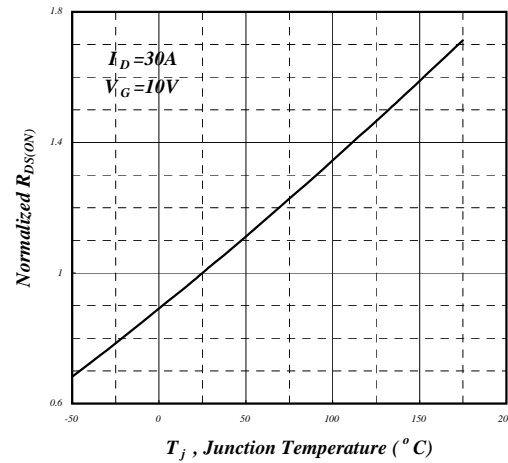


Fig 4. Normalized On-Resistance v.s. Junction Temperature

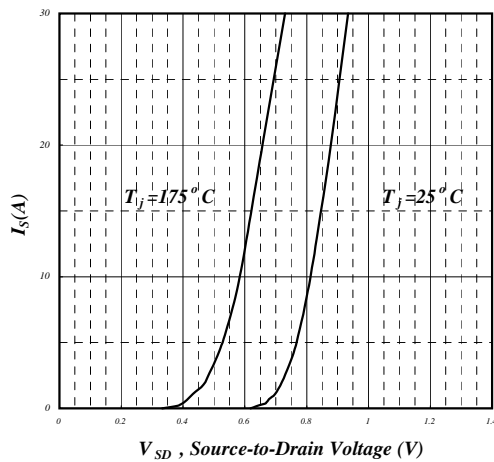


Fig 5. Forward Characteristic of Reverse Diode

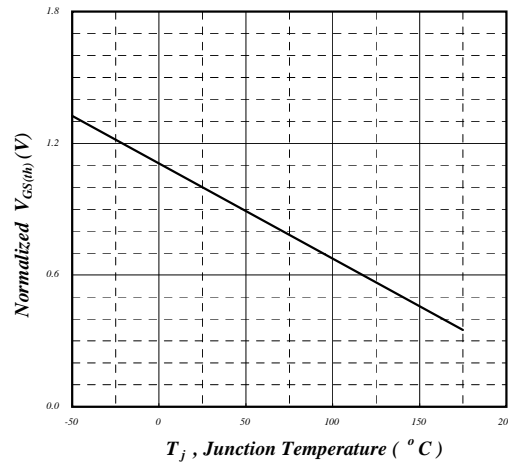


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

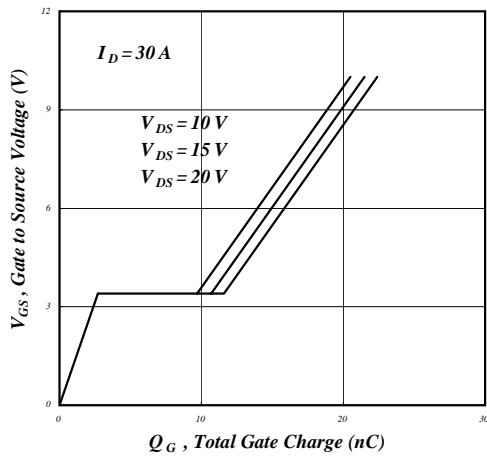


Fig 7. Gate Charge Characteristics

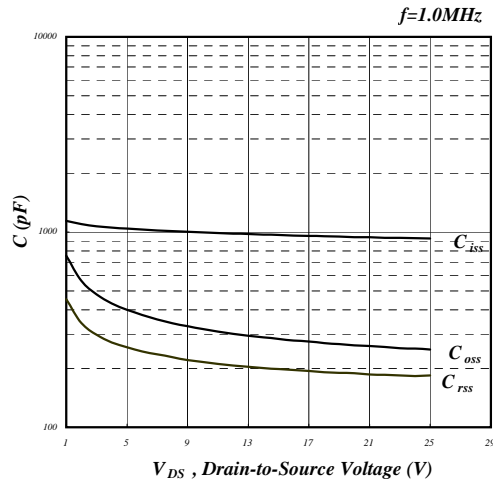


Fig 8. Typical Capacitance Characteristics

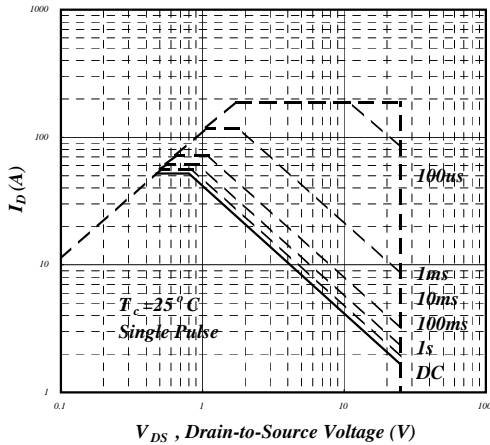


Fig 9. Maximum Safe Operating Area

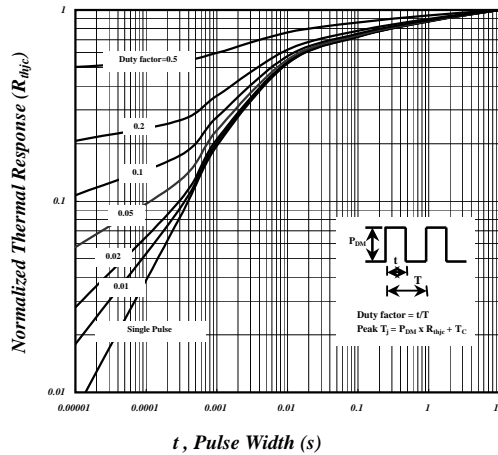


Fig 10. Effective Transient Thermal Impedance

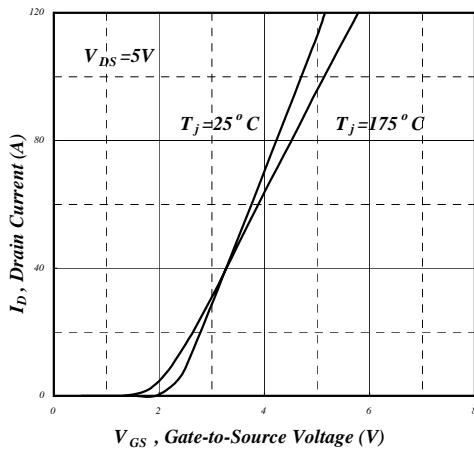


Fig 11. Transfer Characteristics

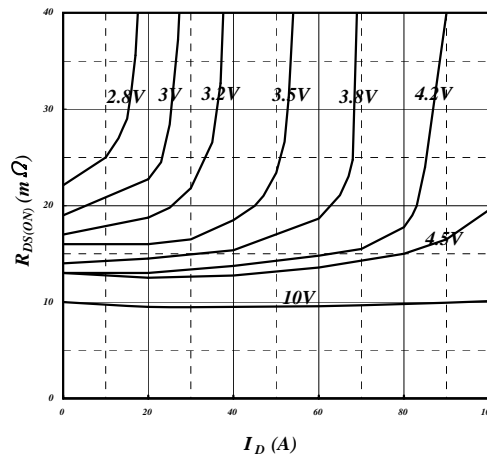


Fig 12. Drain-Source On Resistance

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